

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

<p style="text-align: center;">LED-07</p>	typ. dimensions ( $\mu\text{m}$ )
	typ. thickness 180 $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$  <u>cathode</u> gold alloy, 0.5 $\mu\text{m}$ dotted, 25% covered

## Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.2	1.4	V
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.45	1.8	V
Reverse voltage	$I_R = 100 \mu\text{A}$	$V_R$	5			V
Radiant power <sup>1</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$	2.5	3.5		mW
Radiant power <sup>2</sup>	$I_F = 100 \text{ mA}$	$\Phi_e$		17		mW
Radiant power <sup>3</sup>	$I_F = 100 \text{ mA}$	$\Phi_e$		35		mW
Radiant intensity <sup>1</sup>	$I_F = 20 \text{ mA}$	$I_e$	0.75	1.0		mW/sr
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$	860	875	890	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		45		nm
Switching time	$I_F = 100 \text{ mA}$	$t_r, t_f$		20		ns

<sup>1</sup>Measured on bare chip on TO-18 header

<sup>2</sup>Measured on bare chip on TO-18 header and heat sink

<sup>3</sup>Measured on epoxy chip on TO-18 header and heat sink, 10s current flow (information only)

## Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-875-22				

**Packing:** Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with *EPIGAP* equipment